

FIG. 1

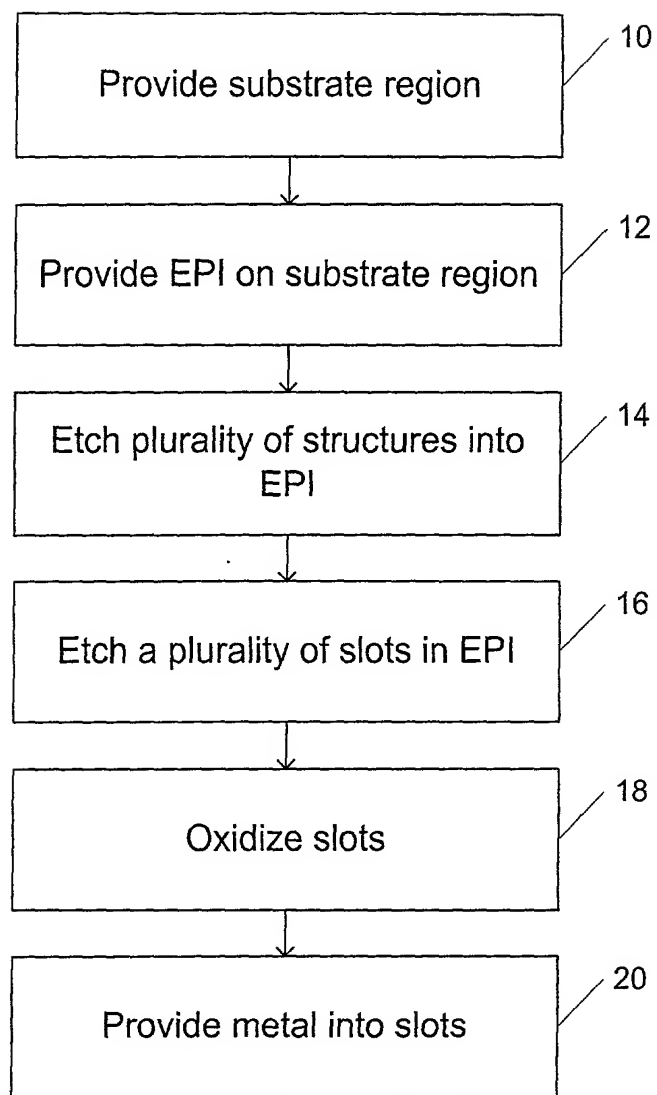


Fig. 1

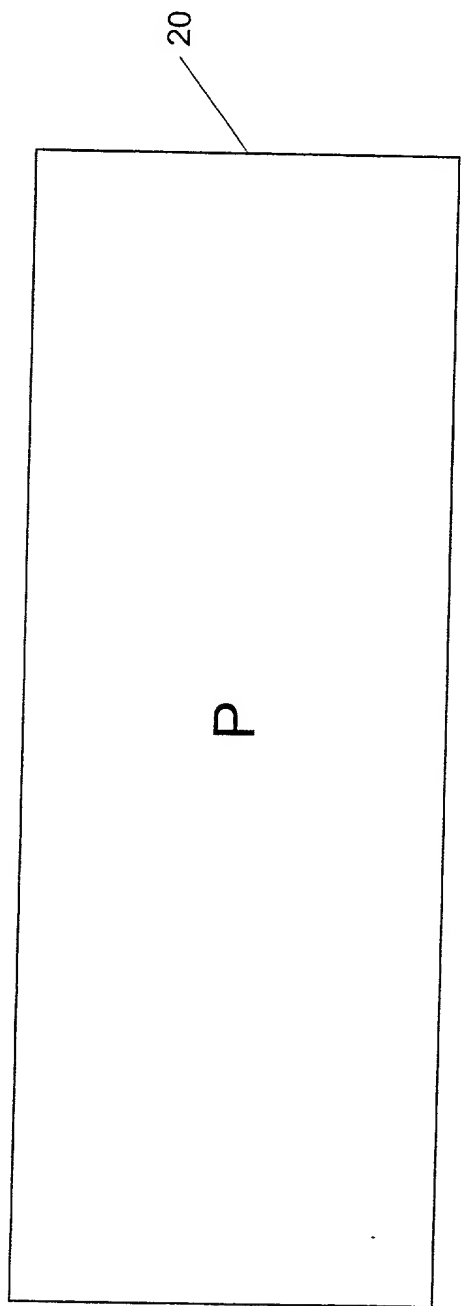


Fig. 2a

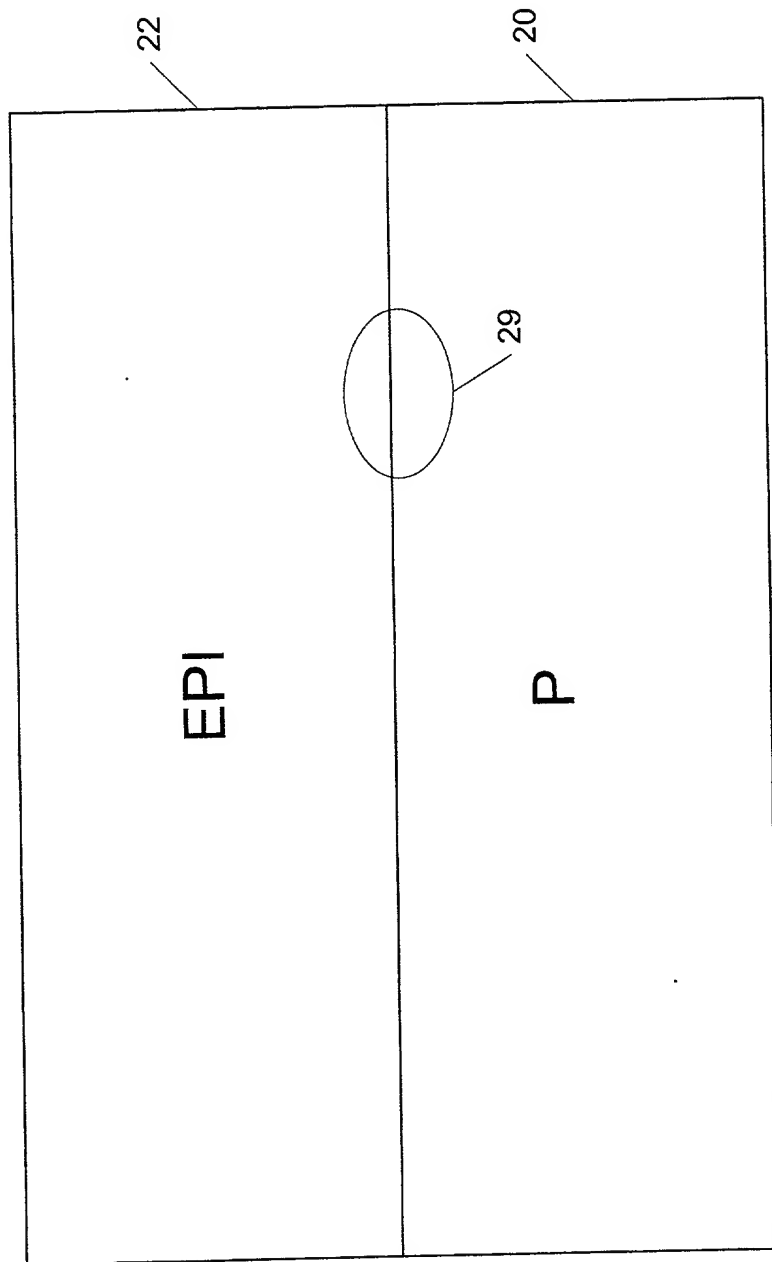


Fig. 2b

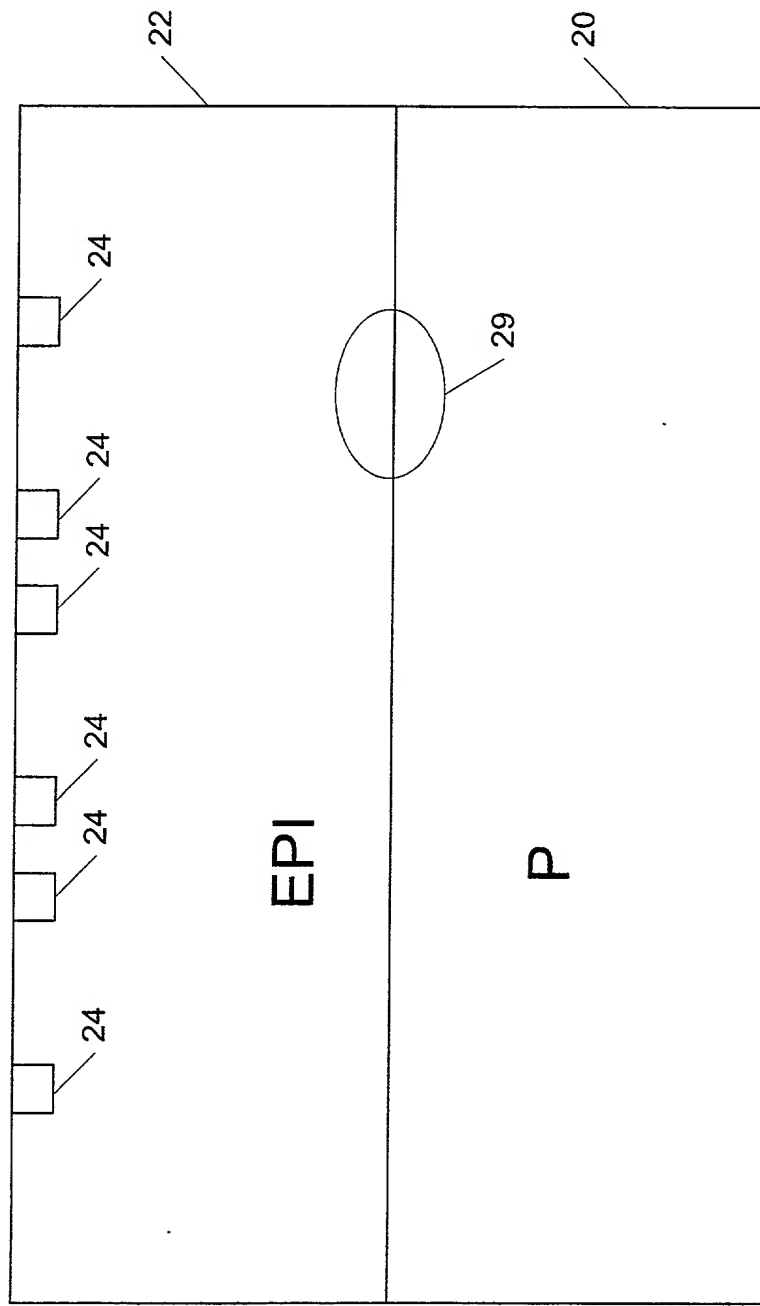


Fig. 2c

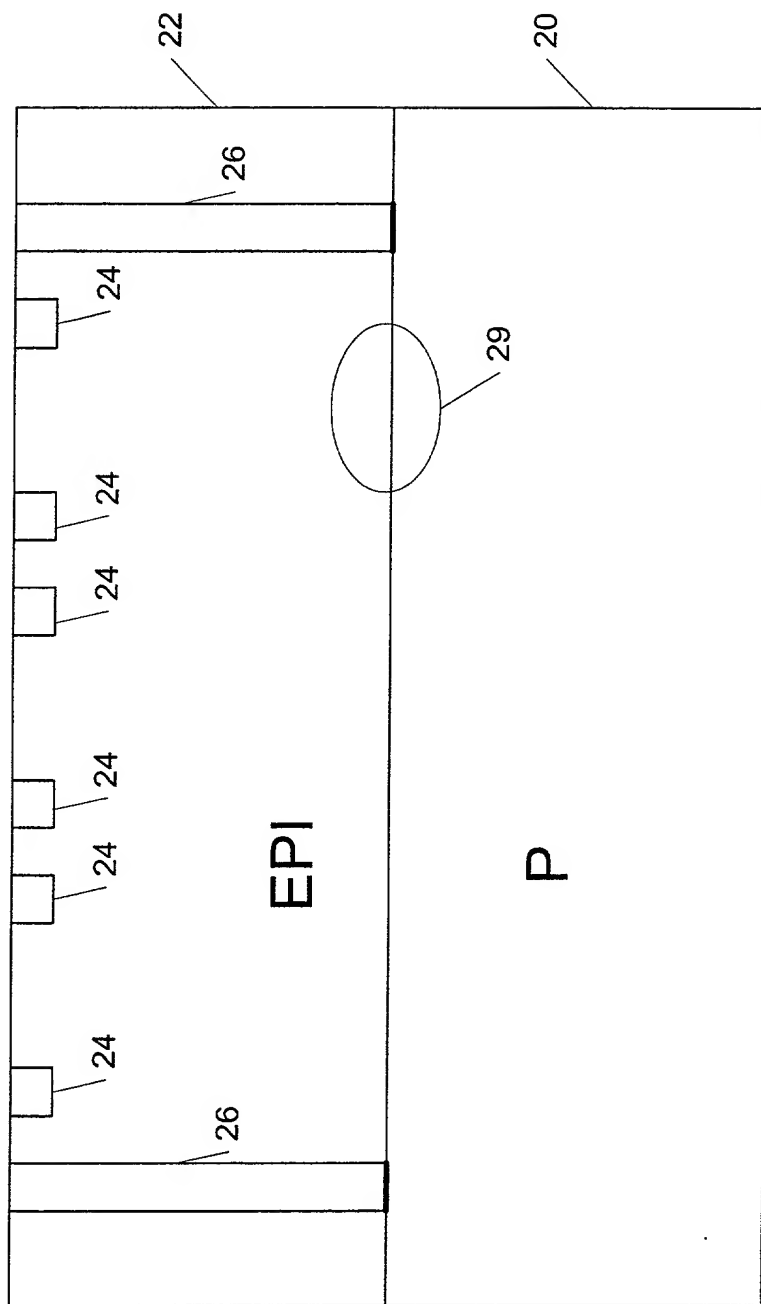


Fig. 2d

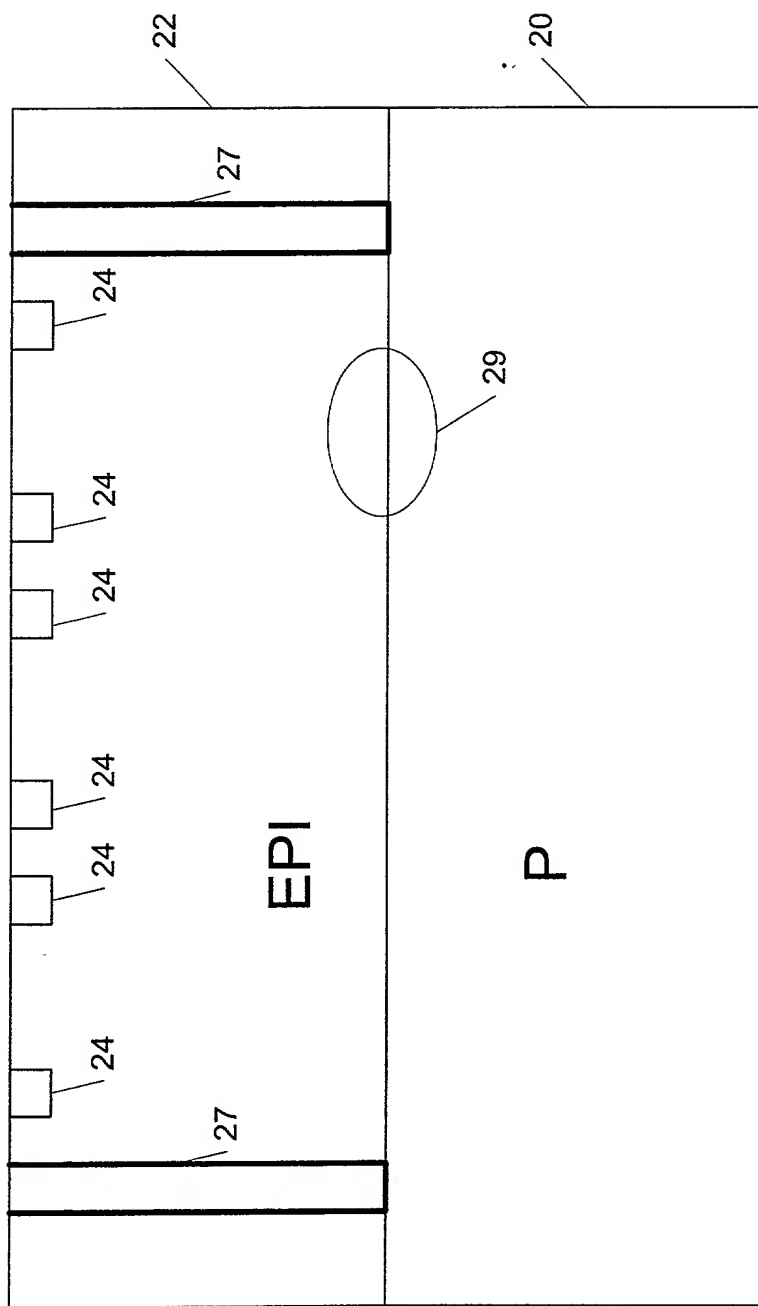


Fig. 2e

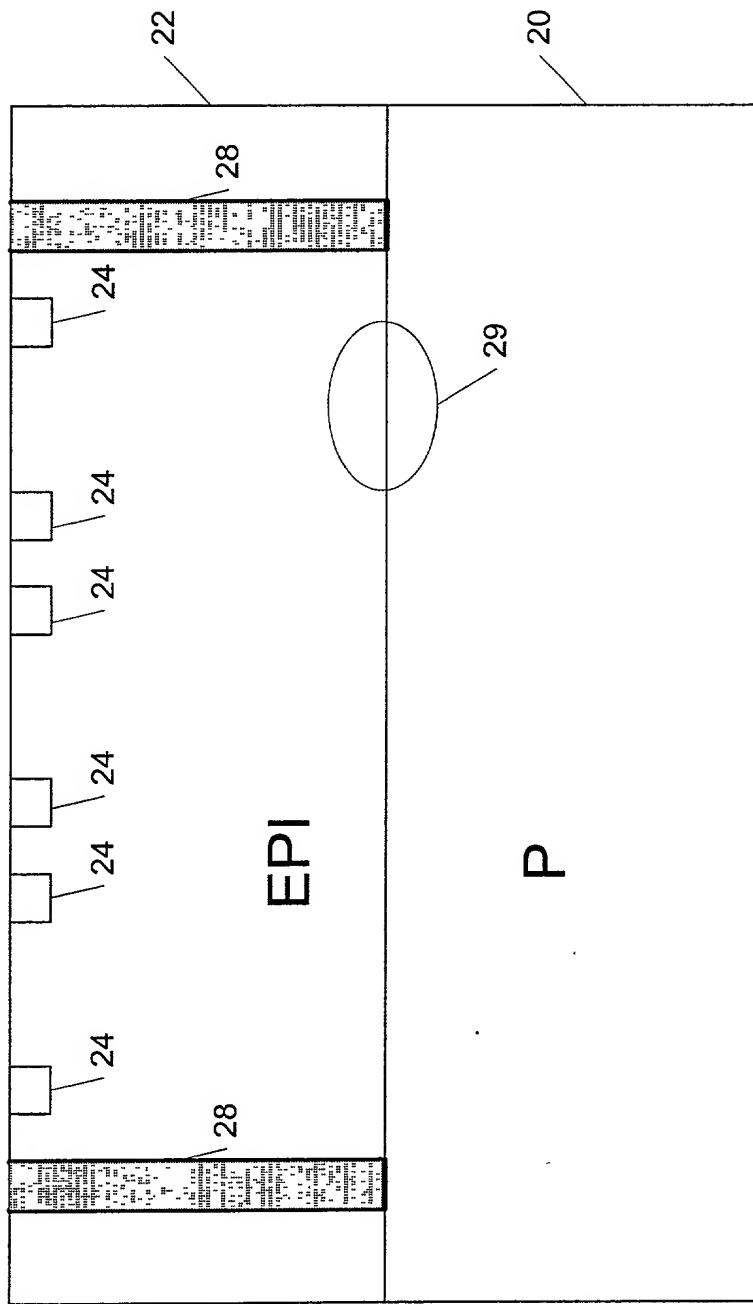


Fig. 2f

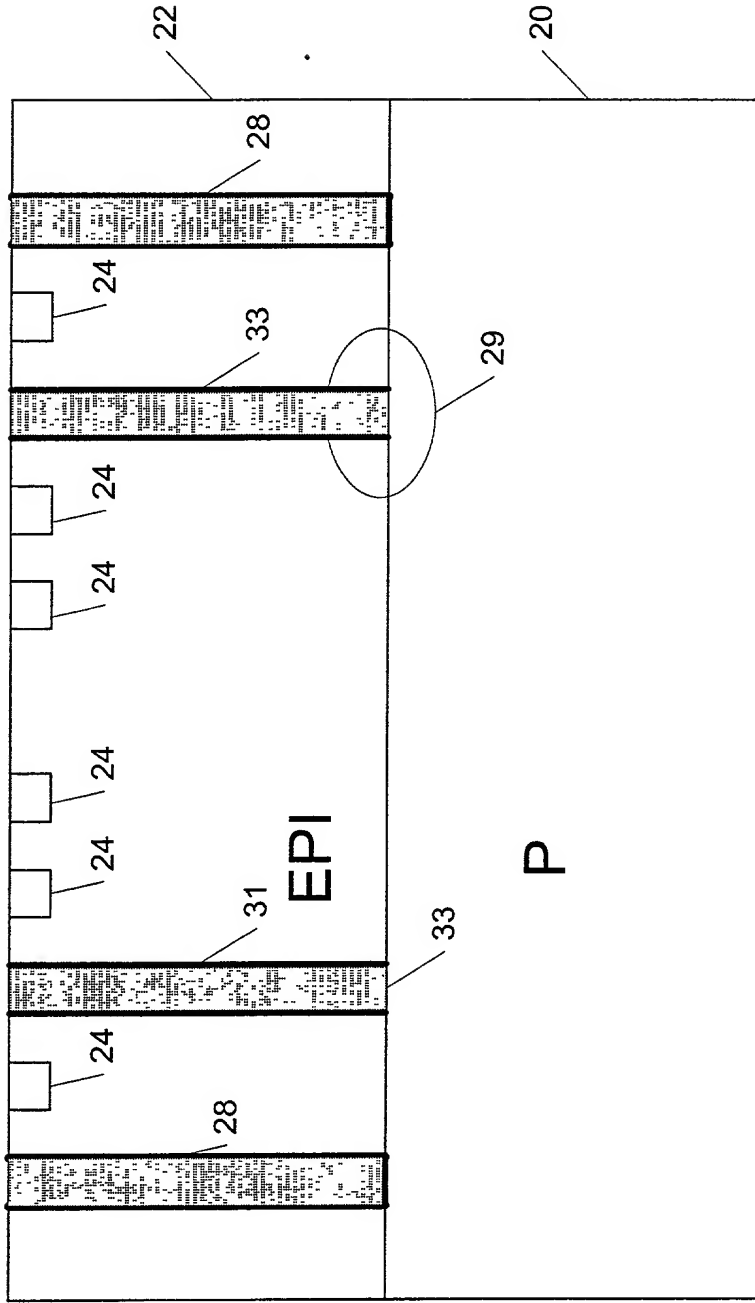


Fig. 2g

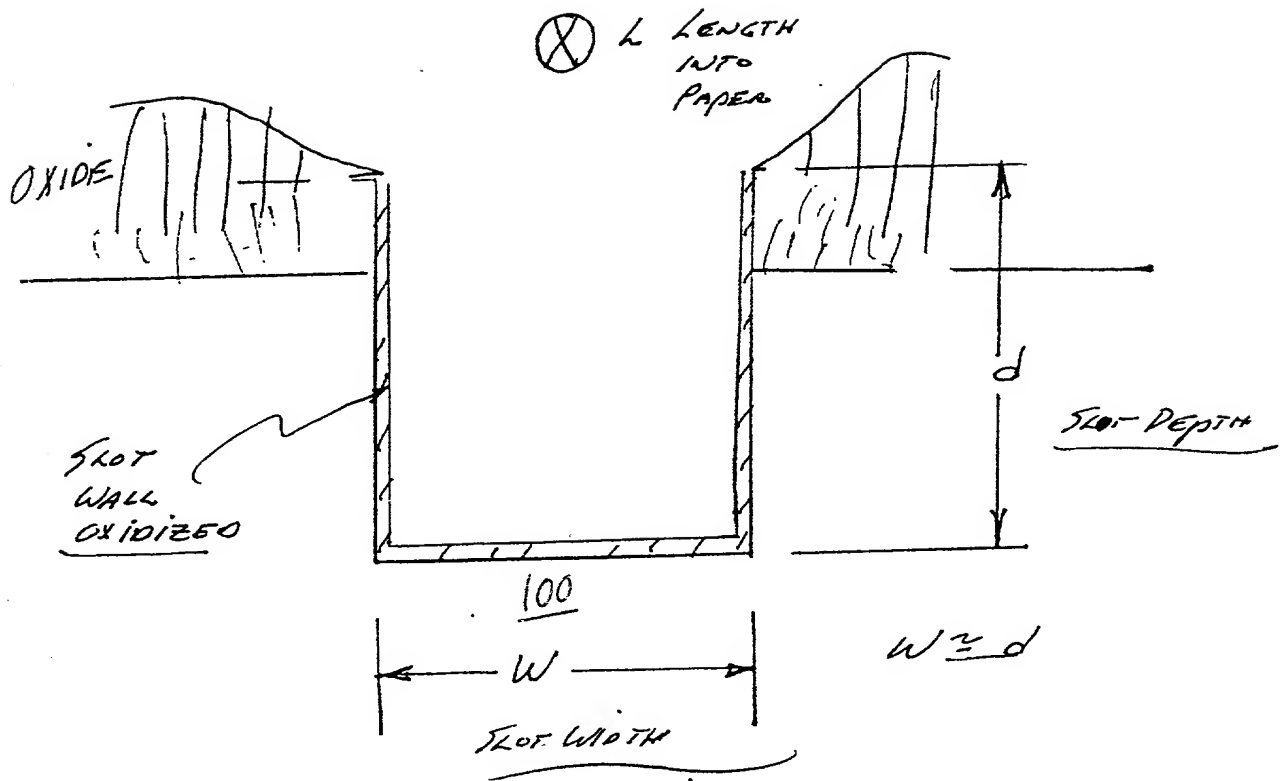


Fig. 3

1003479-10001

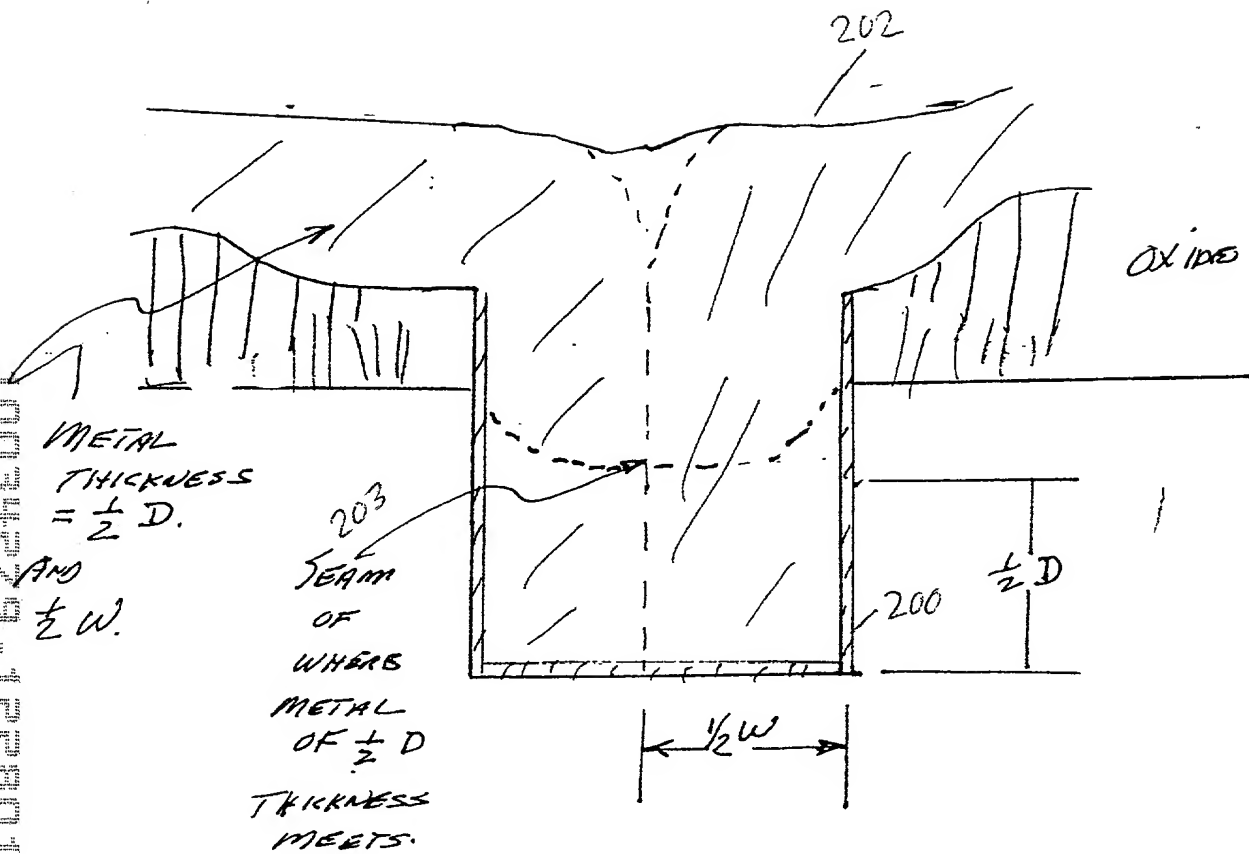
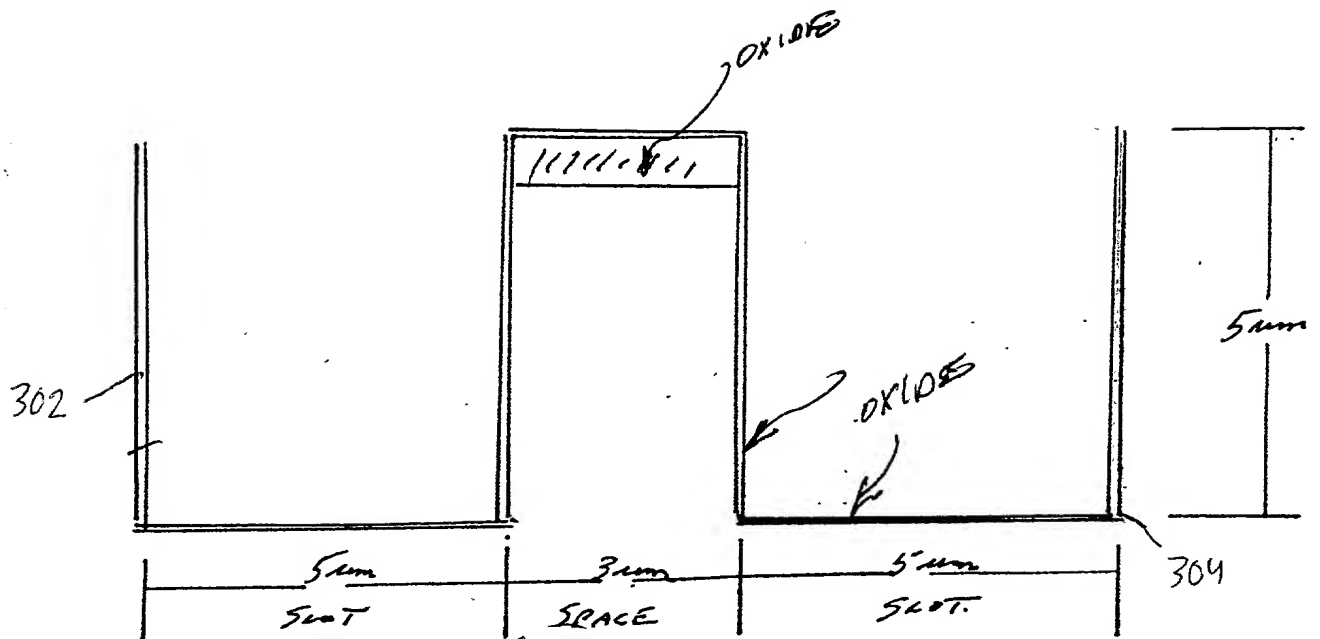
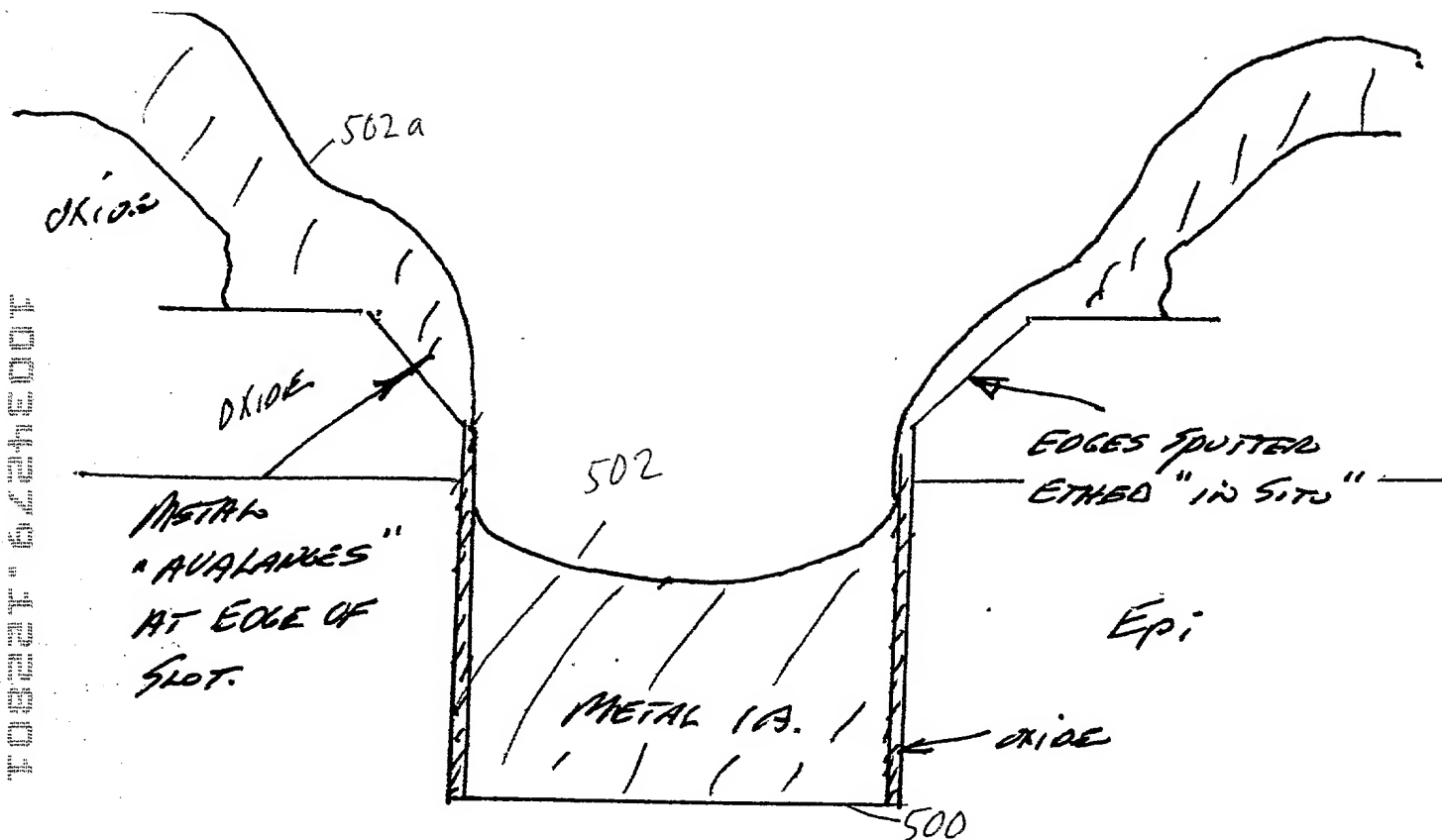


Fig. 4



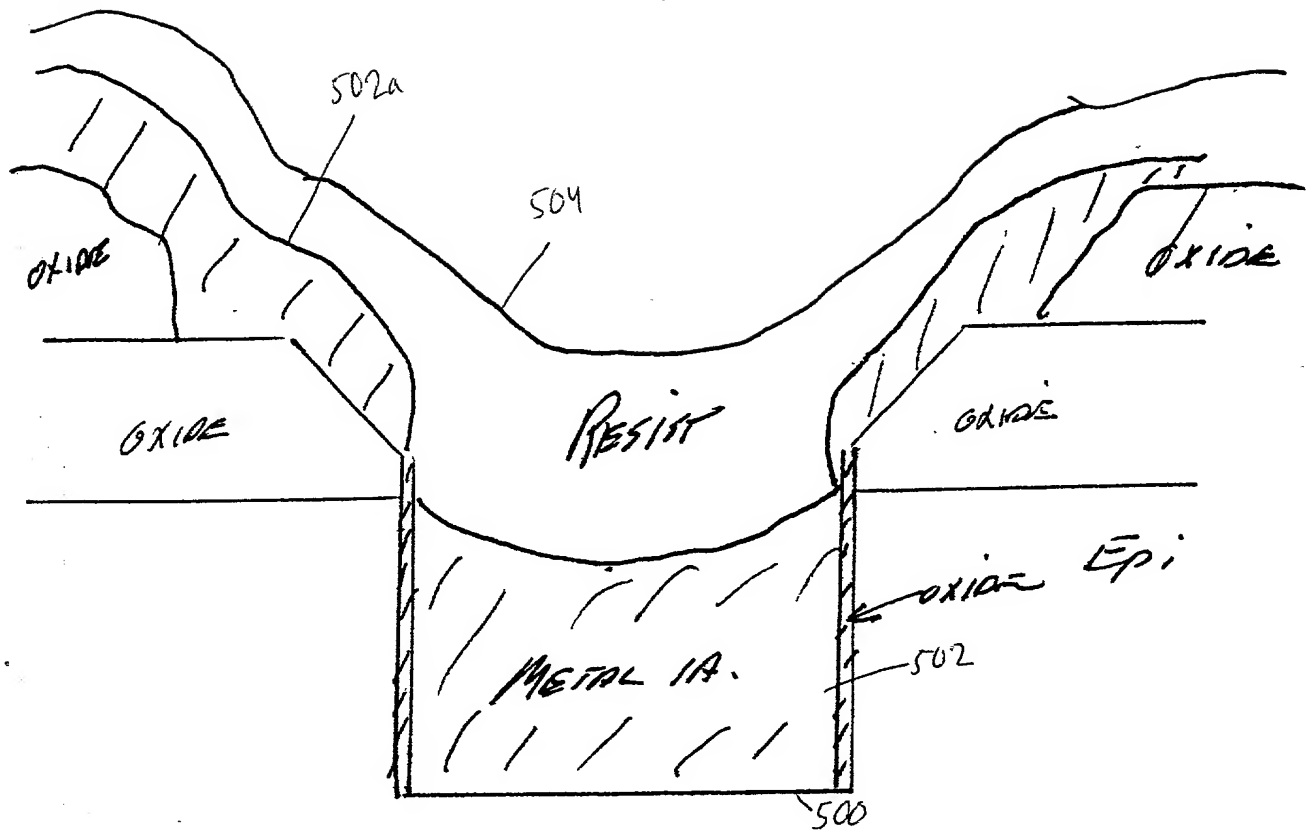
DOUBLE SLOT FOR
DOUBLE WIDTH OF METAL.
3mm SPACE BETWEEN SLOTS

Fig. 4a



Prior TO METAL 1A BEING
 SPUTTERED, THE EDGES OF THE OXIDES
 ARE SPUTTERED ETCHED "IN SITU" &
 1A DEPOSITED

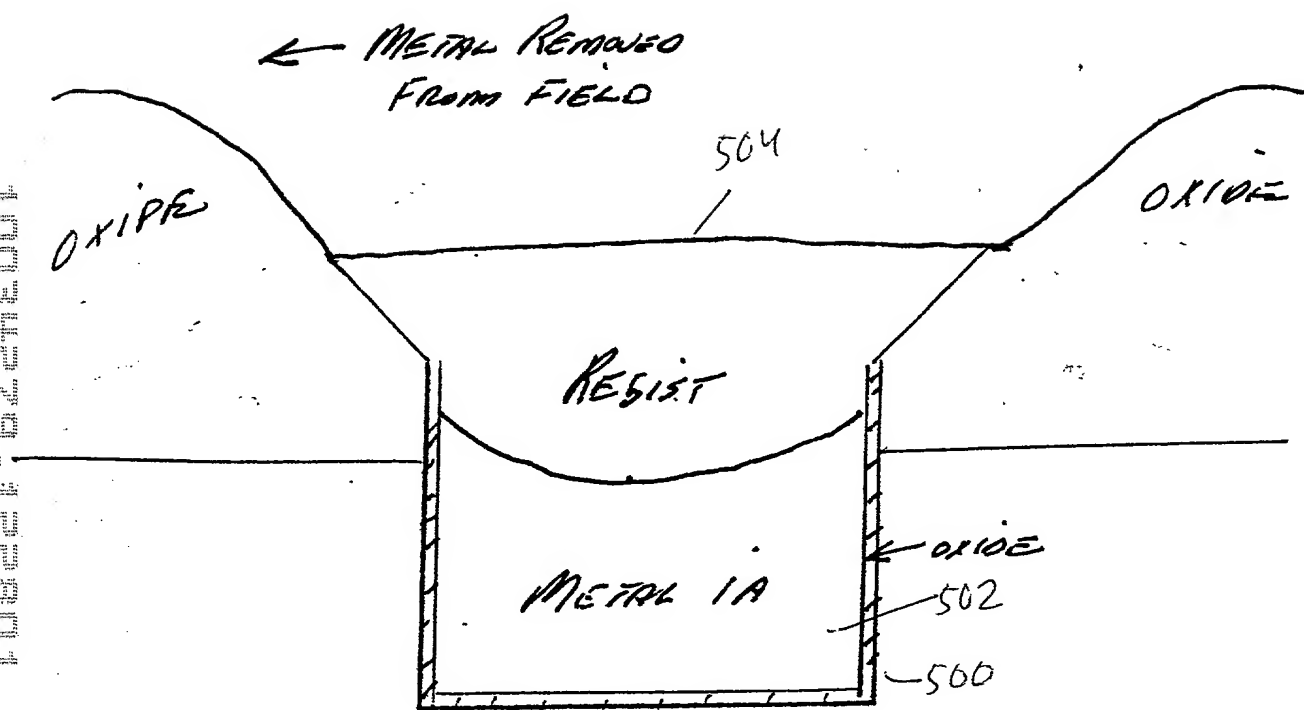
Fig. 5



RESIST COATING - THICK IN THE
SLOTS

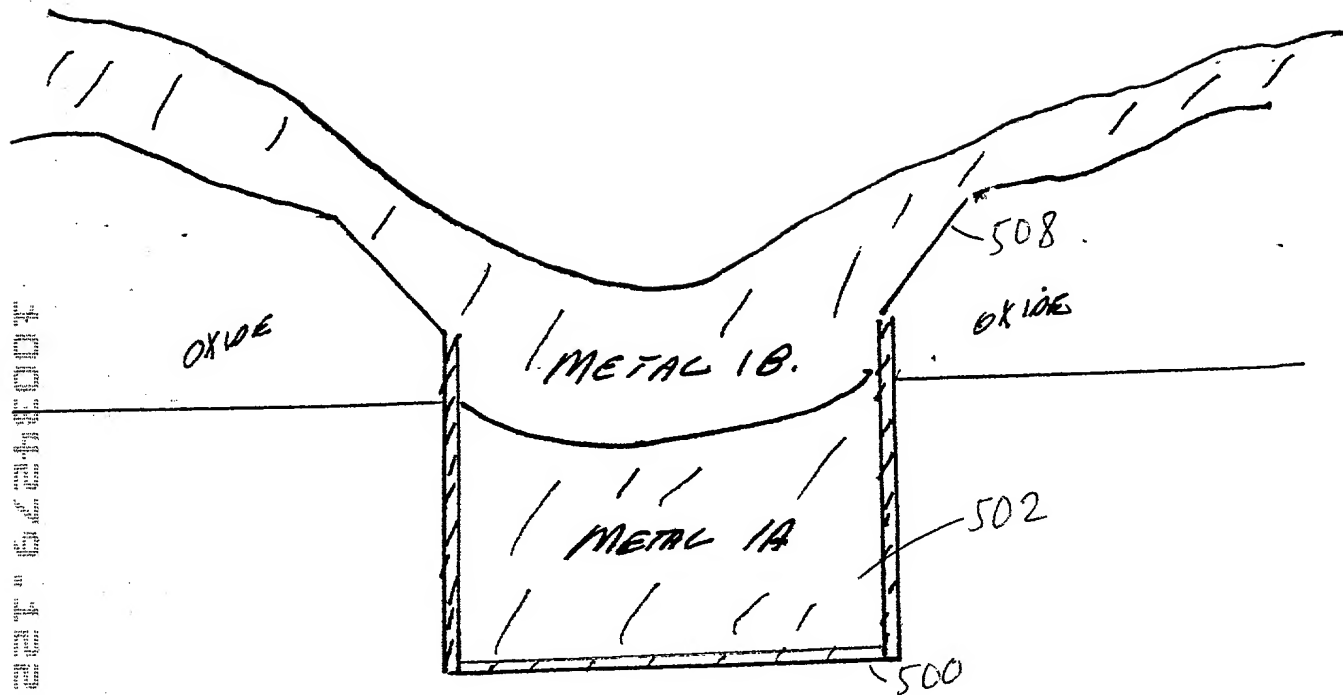
Fig. 6

10034279 122801



RESIST PATTERN ETCHED.
LEAVING RESIST IN TRENCHES
FIELD METAL ETCHED OFF.

Fig-7



RESIST STRIPPED & SECOND
METAL 1B SPUTTER DEPOSITED

Fig. 8

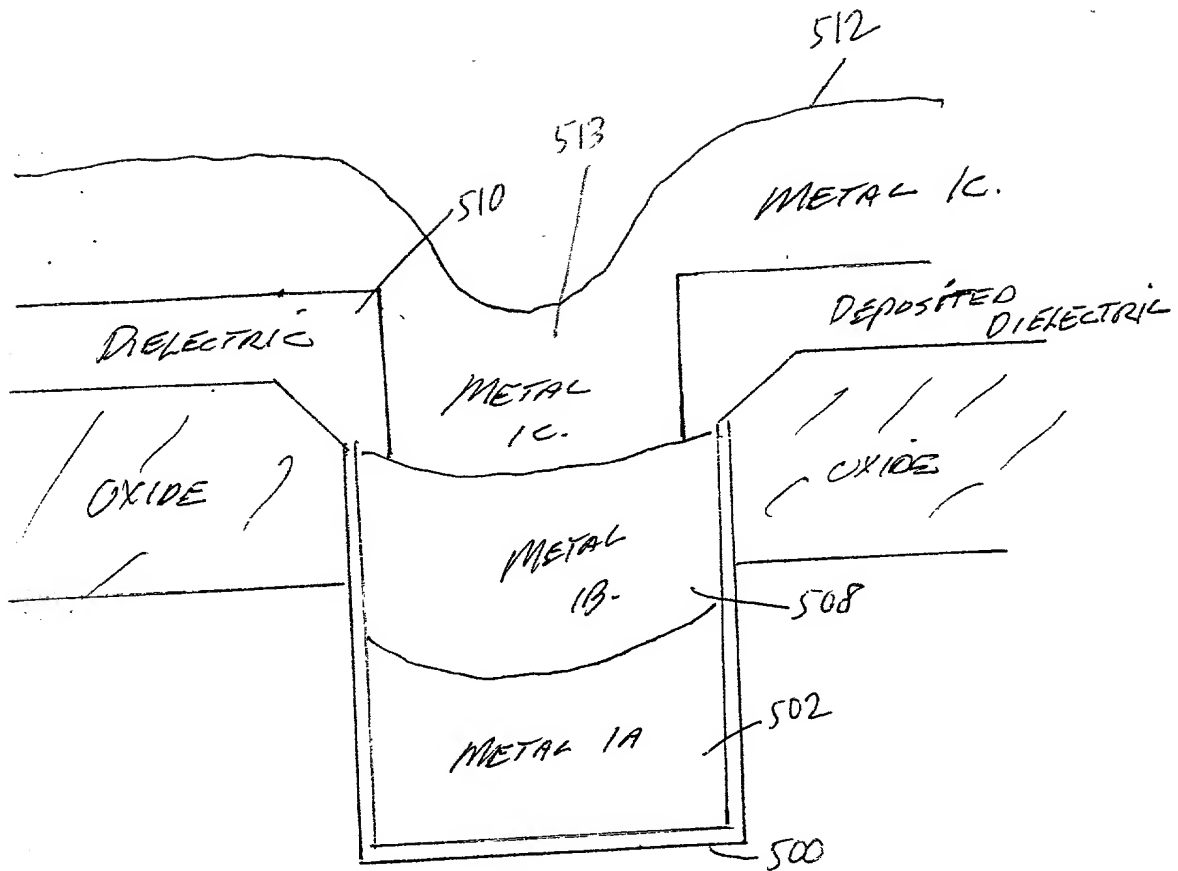


Fig. 9

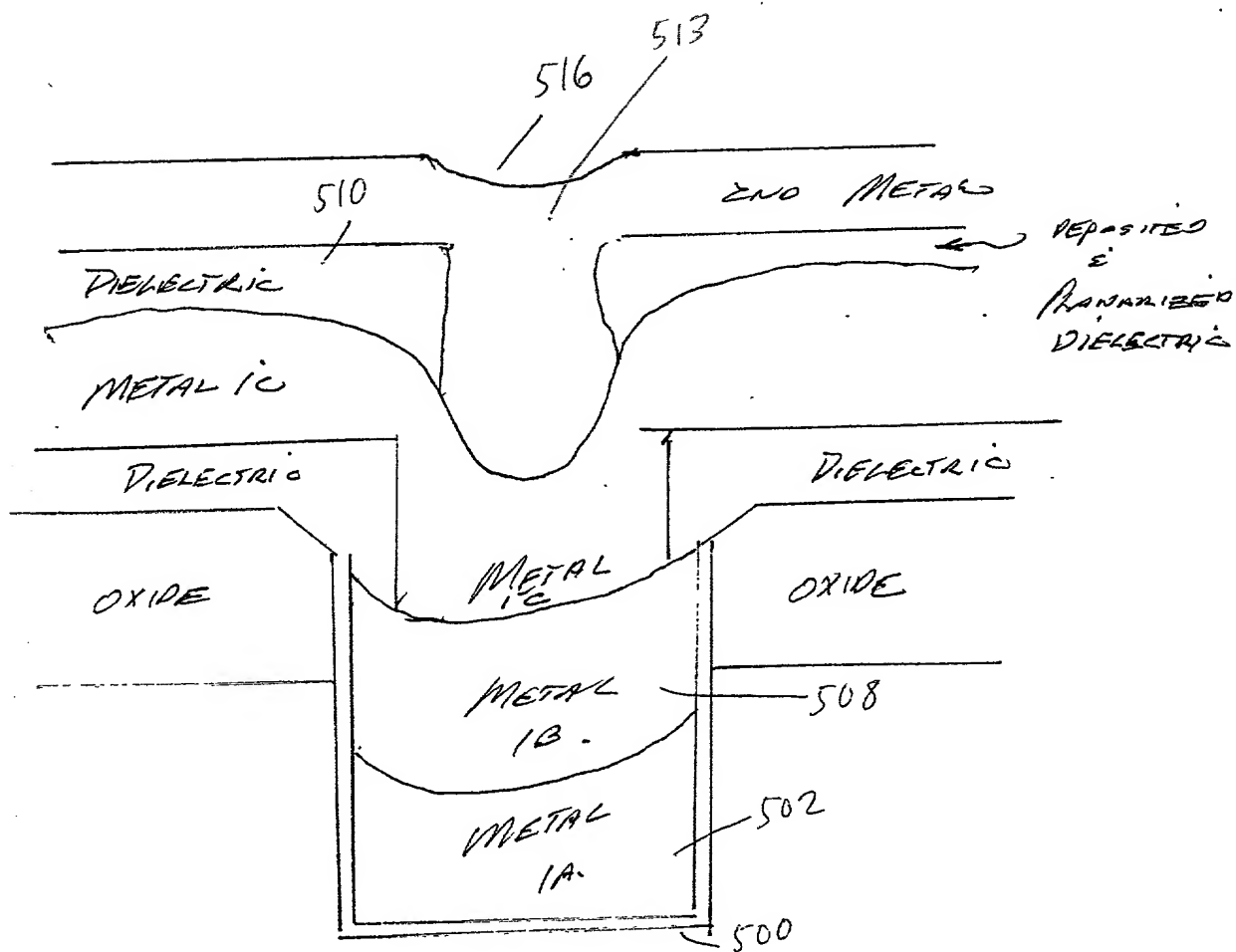
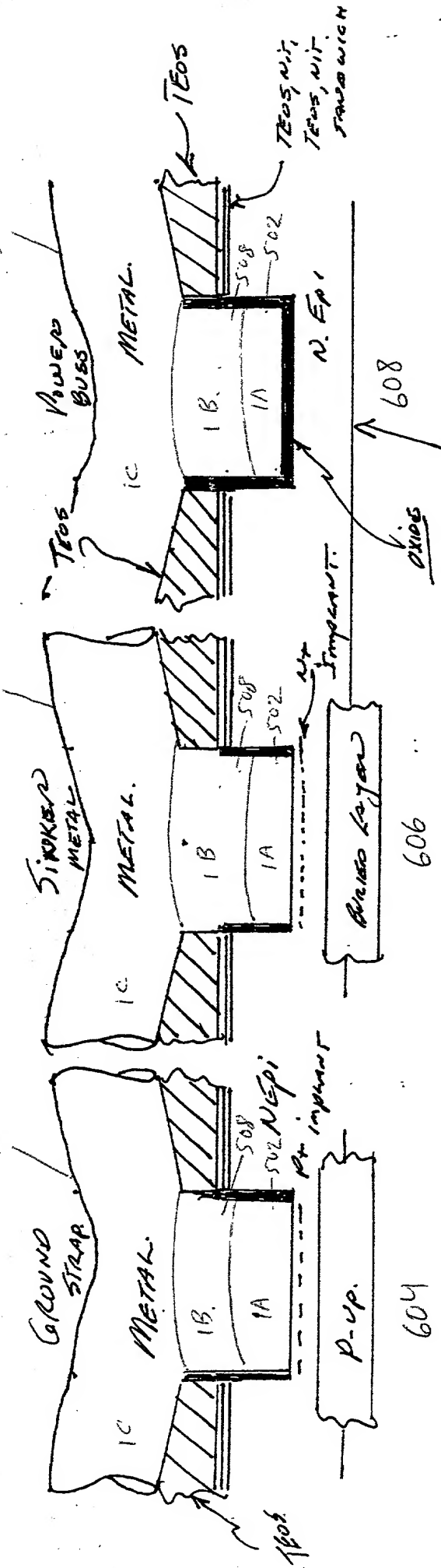


Fig. 10



Ground Strap

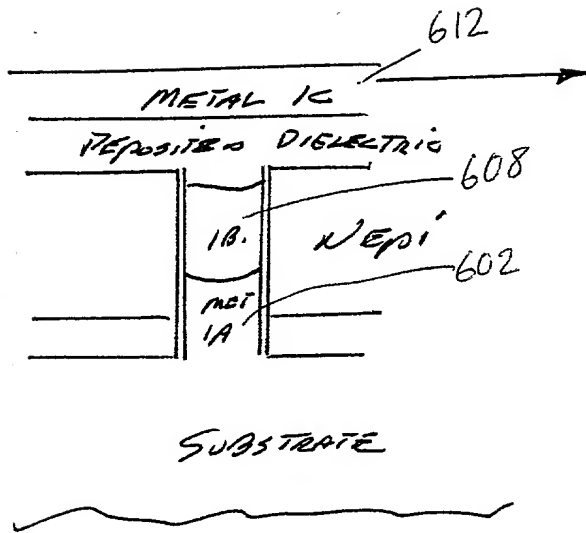
Drain/Bulk Layer / Not Impurant

Power Buss

Ground Strap / Power Buss / Drain Metal Sinkers

Ground Metal Layer of Drain Metal Sinkers
Followed by 9000 Å TEOS - 1015 H.
Not Mass - Metal
Metal 1.5 - 2.0 um deposited

Fig. 11 Power Metal.



METAL IC
 CONNECTS AN ISOLATED
 ISLAND TO ADJACENT
 ISOLATED EPI ISLANDS
 AND CROSSES OVER THE
 ISOLATION GROUND
 STRAP BY NOT OPENING
 A VIA IN THIS PORTION
 TO ALLOW IC TO BE
 ISOLATED FROM GROUND.

Fig. 12